

N-channel 40 V, 1.7 mΩ logic level MOSFET in SOT78 1 February 2013

Product data sheet

1. **General description**

Logic level N-channel MOSFET in SOT78 using TrenchMOS technology. Product design and manufacture has been optimized for use in battery operated power tools.

Features and benefits 2.

- High efficiency due to low switching & conduction losses •
- Robust construction for demanding applications
- Logic level gate

Applications 3.

- Battery-powered tools •
- Load switching
- Motor control
- Uninterruptible power supplies

4. Quick reference data

Table 1. Qu	uick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	[1]	-	-	150	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	349	W
Static charac	cteristics			- 1		-	,
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u>		-	1.4	1.7	mΩ
Dynamic cha	aracteristics	·					,
Q _{G(tot)}	total gate charge	V_{GS} = 10 V; I _D = 25 A; V _{DS} = 32 V;		-	230	-	nC
Q _{GD}	gate-drain charge	<u>Fig. 13; Fig. 14</u>		-	40.9	-	nC
Avalanche ru	uggedness	·					,
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$\label{eq:ID} \begin{array}{l} I_D = 150 \text{ A}; \ V_{sup} \leq 40 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} = 10 \text{ V}; \ T_{j(init)} = 25 \ ^\circ\text{C}; \ unclamped; \\ \hline \text{Fig. 3} \end{array}$		-	-	801.1	mJ

[1] Continuous current is limited by package.

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5. Pinning information

Table 2. Pinning information							
Pin	Symbol	Description	Simplified outline	Graphic symbol			
1	G	gate	mb	D			
2	D	drain	$2 \circ 4$				
3	S	source	TO-220AB (SOT78)	G G M M M M M M M M M M M M M M M M M M			

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PSMN1R9-40PL	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN1R9-40PL	PSMN1R9-40PL

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	40	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	40	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	150	А
		T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	150	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4		-	1332	А

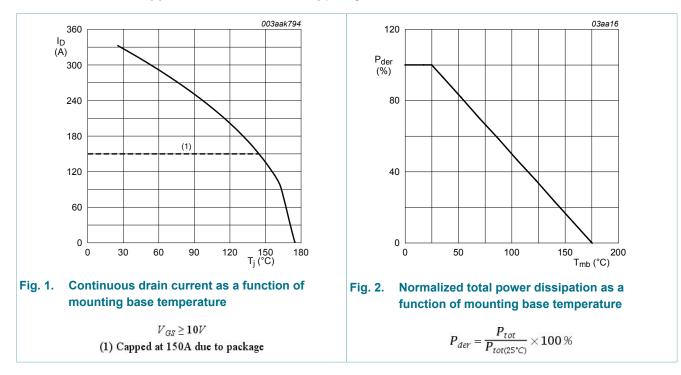
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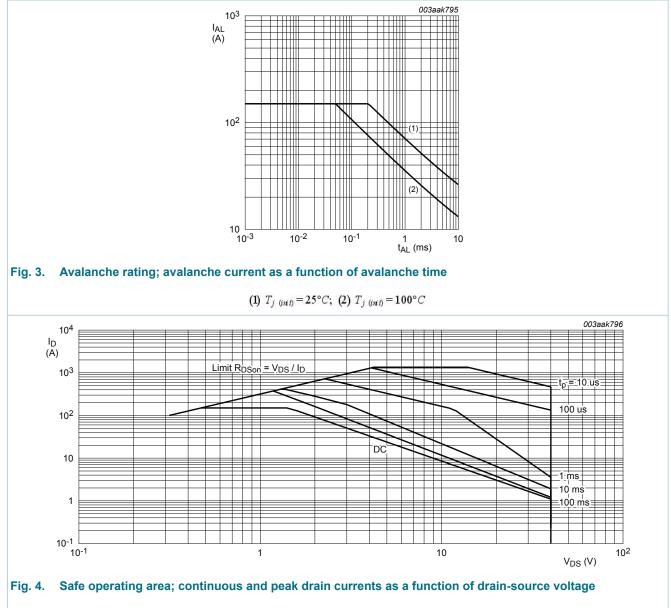
Symbol	Parameter	Conditions		Min	Мах	Unit
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	349	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain	diode					_
I _S	source current	T _{mb} = 25 °C	[1]	-	150	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1332	А
Avalanche ru	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} {\sf I}_{\sf D} = 150 \; {\sf A}; \; {\sf V}_{sup} \le 40 \; {\sf V}; \; {\sf R}_{\sf GS} = 50 \; \Omega; \\ {\sf V}_{\sf GS} = 10 \; {\sf V}; \; {\sf T}_{j(init)} = 25 \; {\rm ^{\circ}C}; \; unclamped; \\ \hline {\sf Fig. 3} \end{array}$		-	801.1	mJ



[1] Continuous current is limited by package.

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 $T_{mb} = 25^{\circ}C; \ I_{DM}$ is a single pulse

9. Thermal characteristics

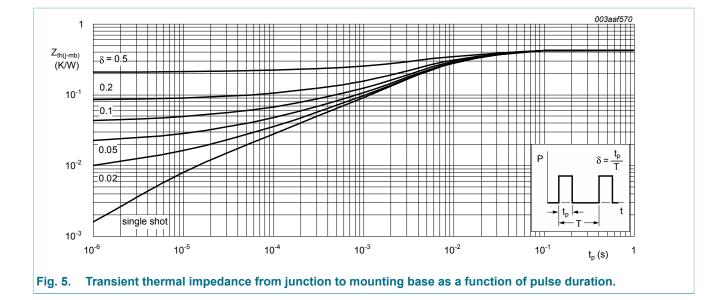
Fable 6. Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	0.35	0.43	K/W	
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in still air		-	60	-	K/W	

Table 6. Thermal characteristic

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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	40	-	-	V
breal	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	36	-	-	V
V _{GS(th)}	/ _{GS(th)} gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	2.45	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 9	0.5	-	-	V
I _{DSS} drain leakag	drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C	-	0.13	1	μA
		V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	on drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	1.4	1.7	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	1.65	1.94	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	3.15	mΩ
R _G	gate resistance	f = 1 MHz	0.38	0.76	1.52	Ω

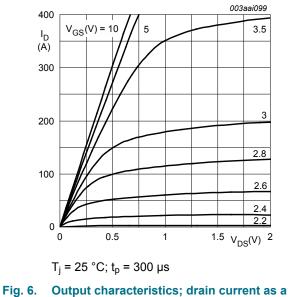
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cl	haracteristics	· · · · · ·				
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 32 V; V _{GS} = 5 V; Fig. 13; Fig. 14	-	120	-	nC
		I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V;	-	230	-	nC
Q _{GS}	gate-source charge	<u>Fig. 13; Fig. 14</u>	-	26.9	-	nC
Q _{GD}	gate-drain charge		-	40.9	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 15</u>	-	13200	-	pF
C _{oss}	output capacitance		-	1530	-	pF
C _{rss}	reverse transfer capacitance		-	740	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 5 V; R _{G(ext)} = 5 Ω	-	95	-	ns
t _r	rise time		-	118	-	ns
t _{d(off)}	turn-off delay time	-	-	195	-	ns
t _f	fall time		-	119	-	ns
Source-dra	in diode				1	
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.77	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 20 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;	-	57	-	ns
Q _r	recovered charge	V _{DS} = 25 V	-	97	-	nC





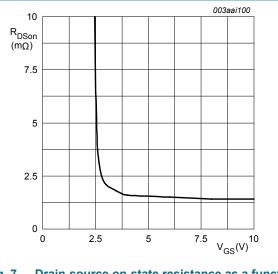


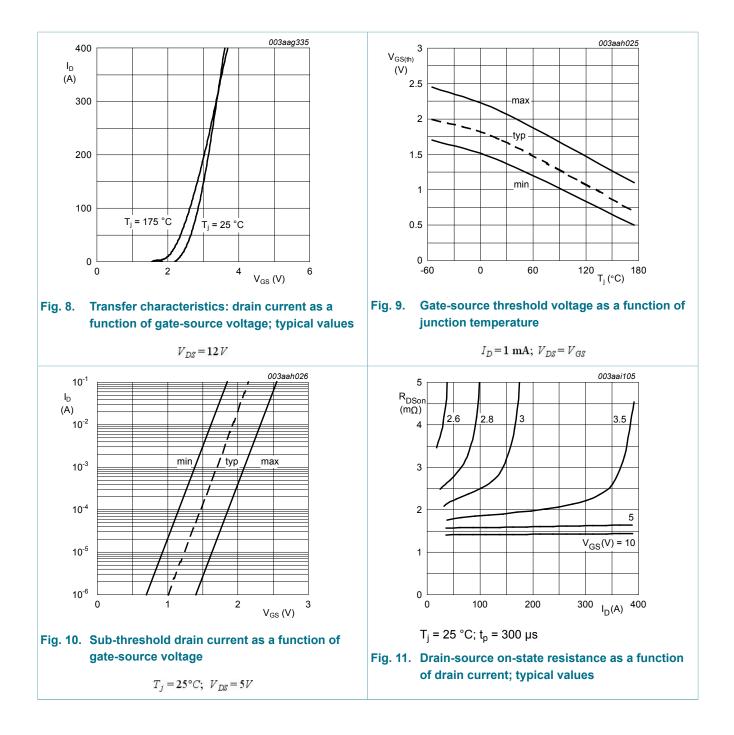
Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 25A$

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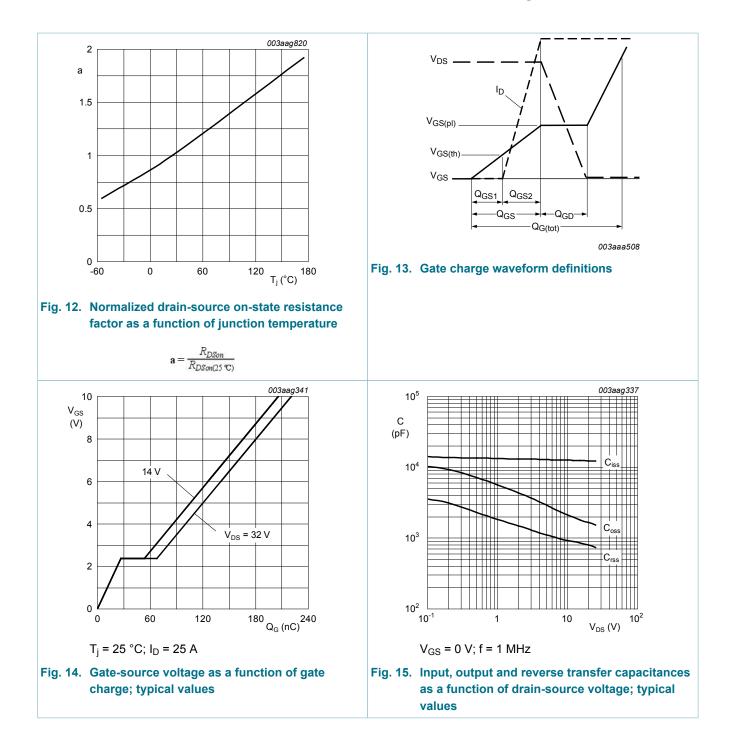


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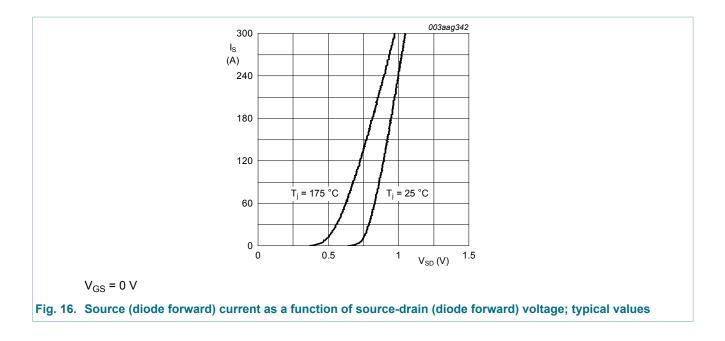
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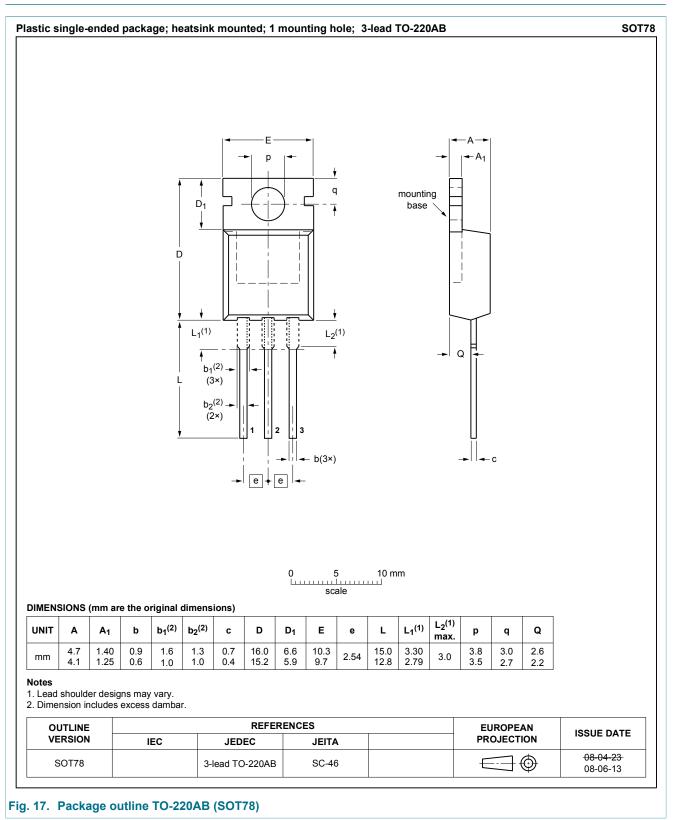
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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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